

## IGBT MODULE ( N series )

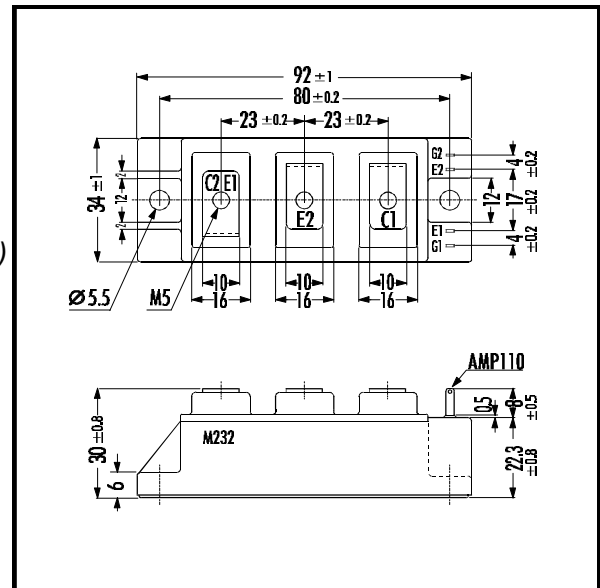
### ■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (~3 Times Rated Current)

### ■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

### ■ Outline Drawing



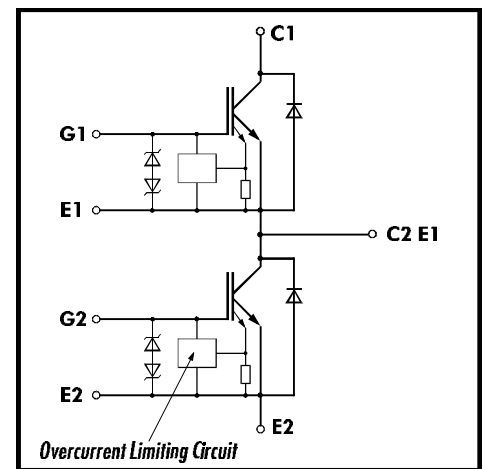
### ■ Maximum Ratings and Characteristics

#### • Absolute Maximum Ratings ( T<sub>c</sub>=25°C )

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V <sub>CE</sub> S	600	V
Gate -Emitter Voltage	V <sub>GE</sub> S	± 20	V
Collector Current	I <sub>C</sub>	150	A
	I <sub>C</sub> PULSE	300	
	-I <sub>C</sub>	150	
	-I <sub>C</sub> PULSE	300	
Max. Power Dissipation	P <sub>C</sub>	600	W
Operating Temperature	T <sub>i</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +125	°C
Isolation Voltage	V <sub>is</sub>	2500	V
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	3.5	

Note: \*1:Recommendable Value; 2.5 ~ 3.5 Nm (M5)

### ■ Equivalent Circuit



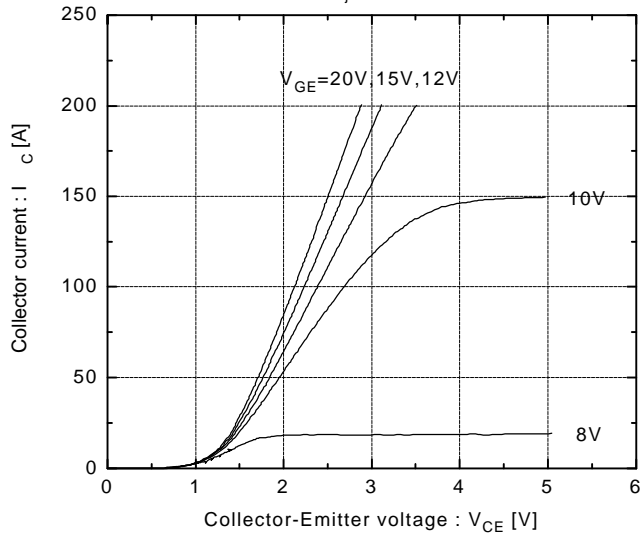
#### • Electrical Characteristics ( at T<sub>j</sub>=25°C )

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I <sub>CES</sub>	V <sub>GE</sub> =0V V <sub>CE</sub> =600V			1.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V V <sub>GE</sub> =± 20V			15	μA
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>GE</sub> =20V I <sub>C</sub> =150mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V I <sub>C</sub> =150A			2.8	V
Input capacitance	C <sub>ies</sub>	V <sub>GE</sub> =0V		9900		pF
Output capacitance	C <sub>oes</sub>	V <sub>CE</sub> =10V		2200		
Reverse Transfer capacitance	C <sub>res</sub>	f=1MHz		1000		
Turn-on Time	t <sub>ON</sub>	V <sub>CC</sub> =300V		0.6	1.2	μs
	t <sub>r</sub>	I <sub>C</sub> =150A		0.2	0.6	
Turn-off Time	t <sub>OFF</sub>	V <sub>GE</sub> =± 15V		0.6	1.0	
	t <sub>f</sub>	R <sub>G</sub> =16Ω		0.2	0.35	
Diode Forward On-Voltage	V <sub>F</sub>	I <sub>F</sub> =150A V <sub>GE</sub> =0V			3.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =150A			300	ns

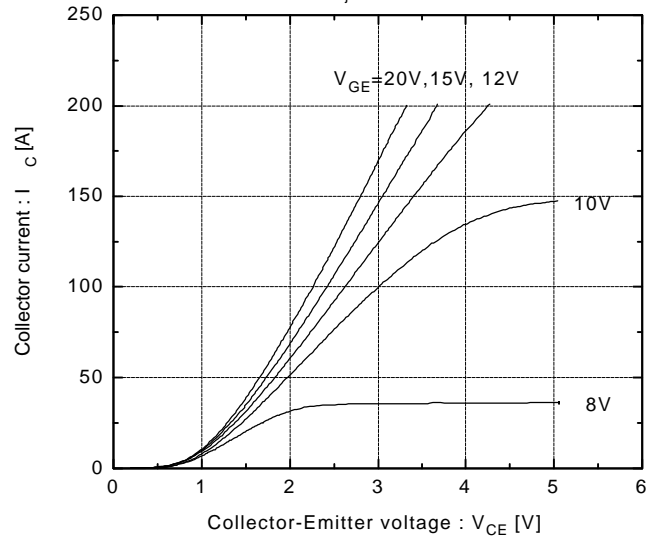
#### • Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R <sub>th(j-c)</sub>	IGBT			0.21	°C/W
	R <sub>th(j-e)</sub>	Diode			0.47	
	R <sub>th(c-f)</sub>	With Thermal Compound		0.05		

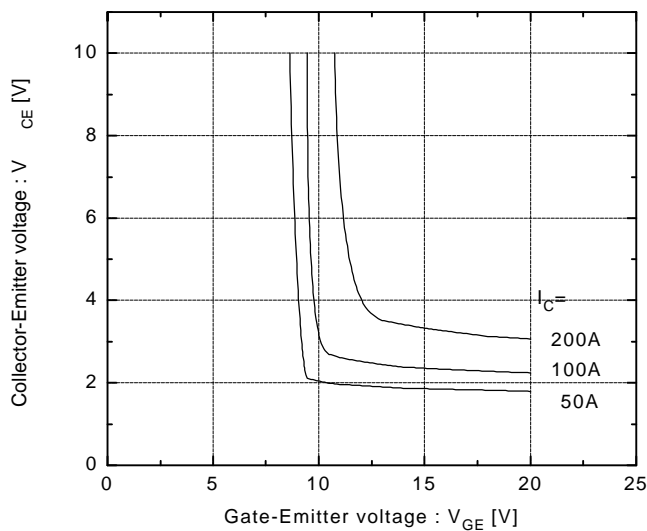
Collector current vs. Collector-Emittor voltage

 $T_j = 25^\circ\text{C}$ 


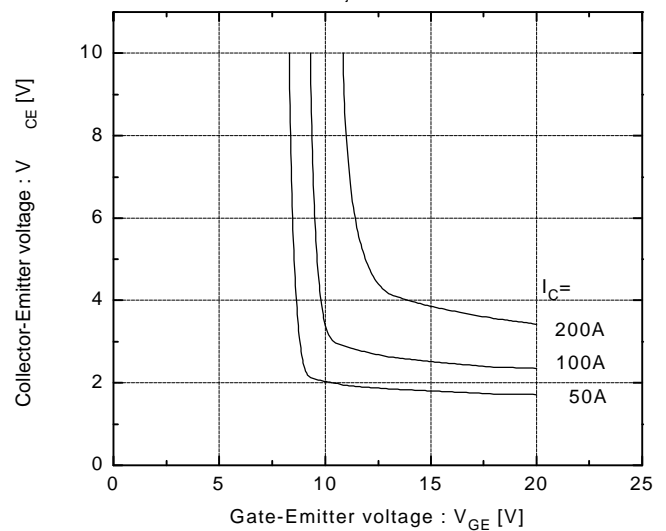
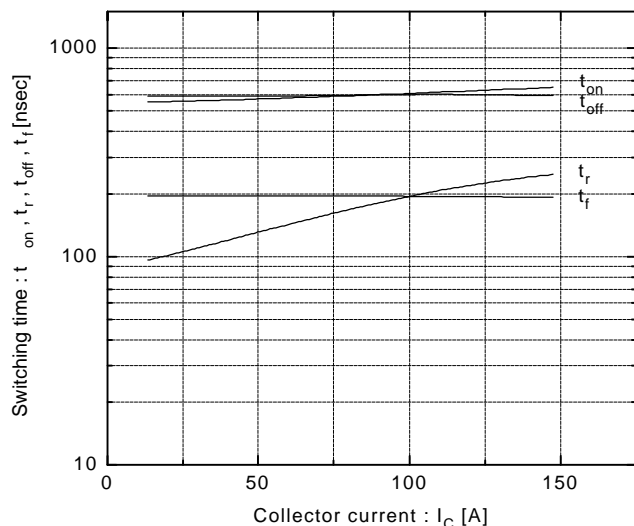
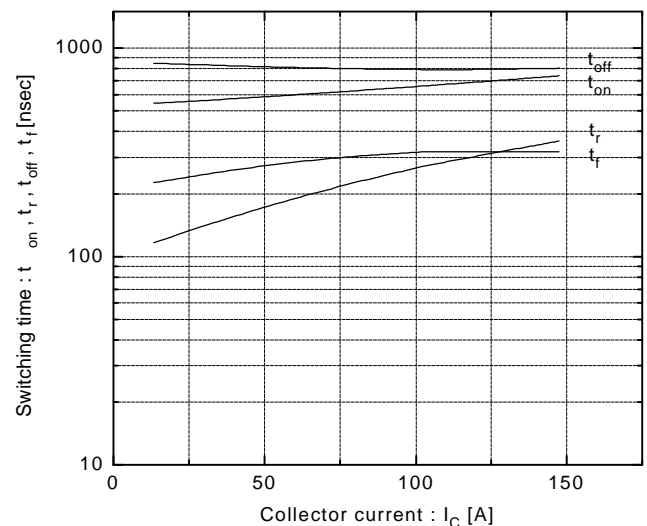
Collector current vs. Collector-Emittor voltage

 $T_j = 125^\circ\text{C}$ 


Collector-Emittor vs. Gate-Emittor voltage

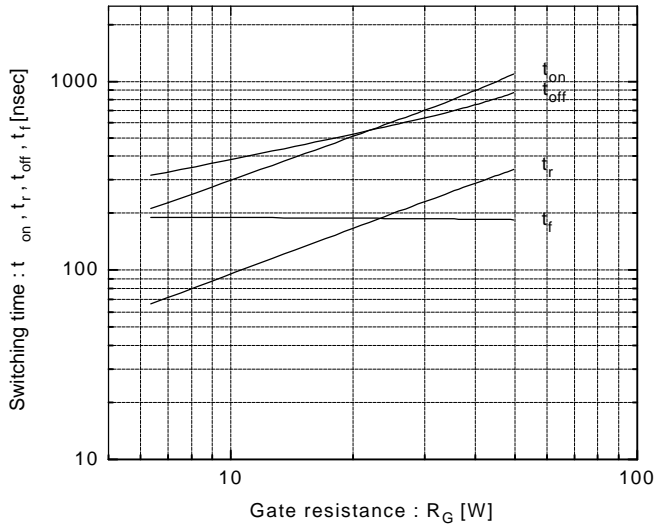
 $T_j = 25^\circ\text{C}$ 


Collector-Emittor vs. Gate-Emittor voltage

 $T_j = 125^\circ\text{C}$ 

 Switching time vs. Collector current  
 $V_{CC}=300\text{V}, R_G=24\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$ 

 Switching time vs. Collector current  
 $V_{CC}=300\text{V}, R_G=24\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$ 


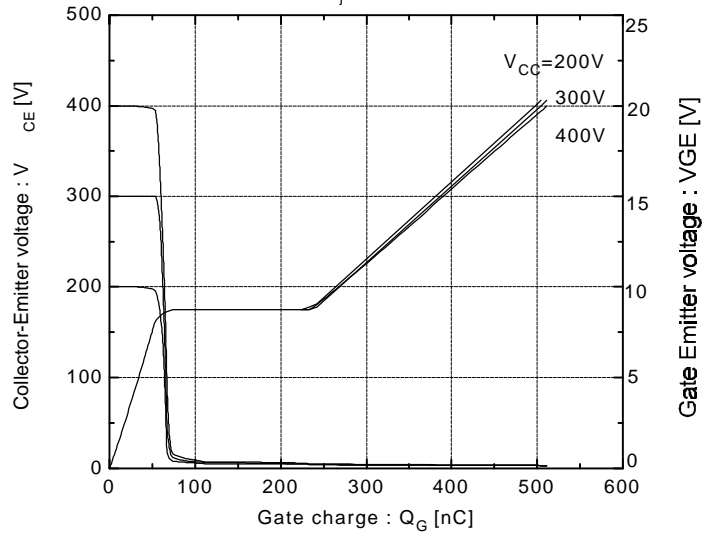
Switching time vs.  $R_G$

$V_{CC}=300V$ ,  $I_C=100A$ ,  $V_{GE}=\pm 15V$ ,  $T_J=25^\circ C$



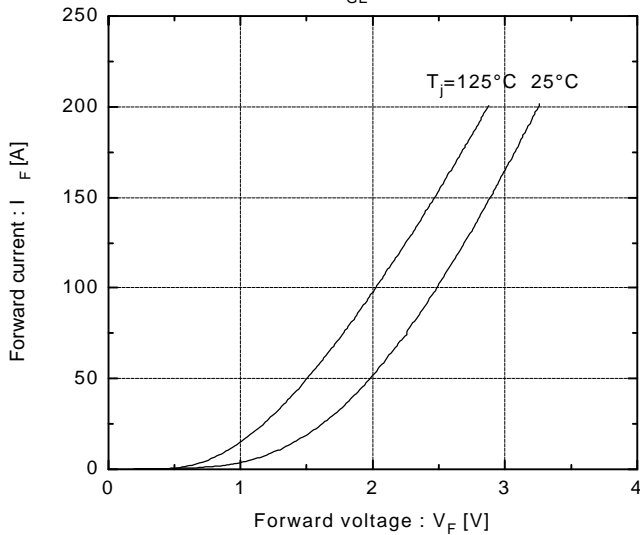
Dynamic input characteristics

$T_J=25^\circ C$



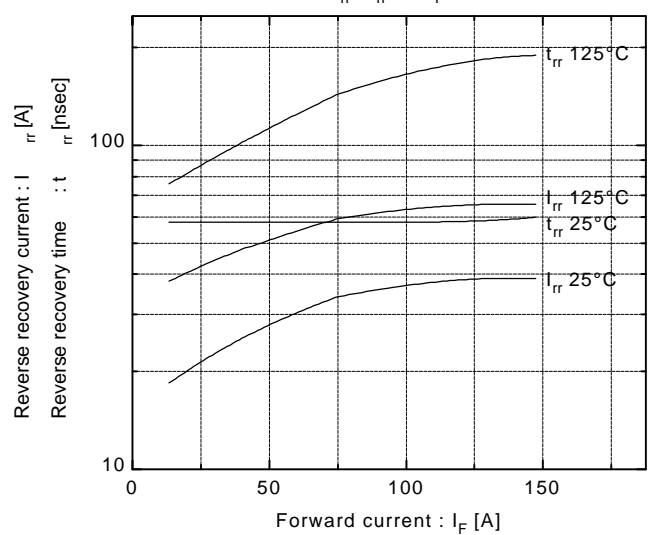
Forward current vs. Forward voltage

$V_{GE}=0V$

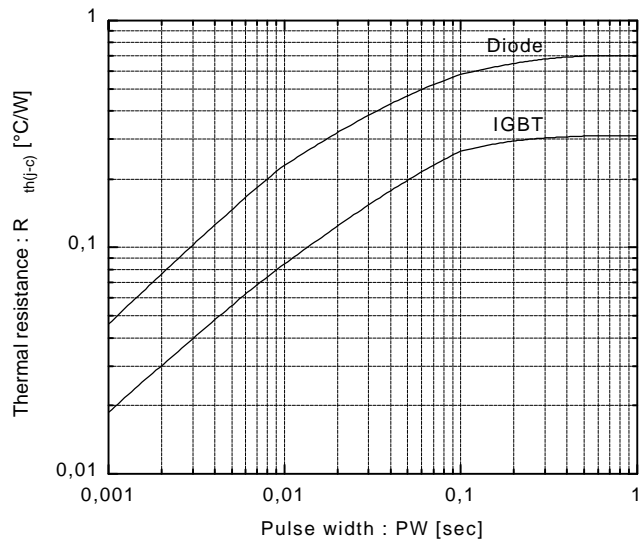


Reverse recovery characteristics

$t_{rr}$ ,  $I_{rr}$  vs.  $I_F$

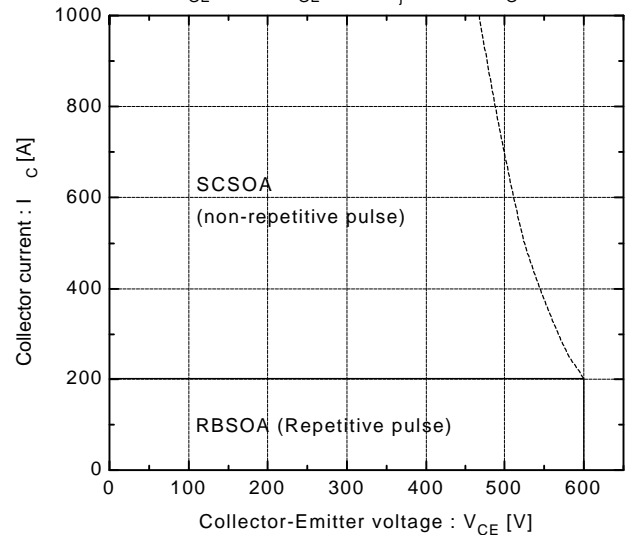


Transient thermal resistance

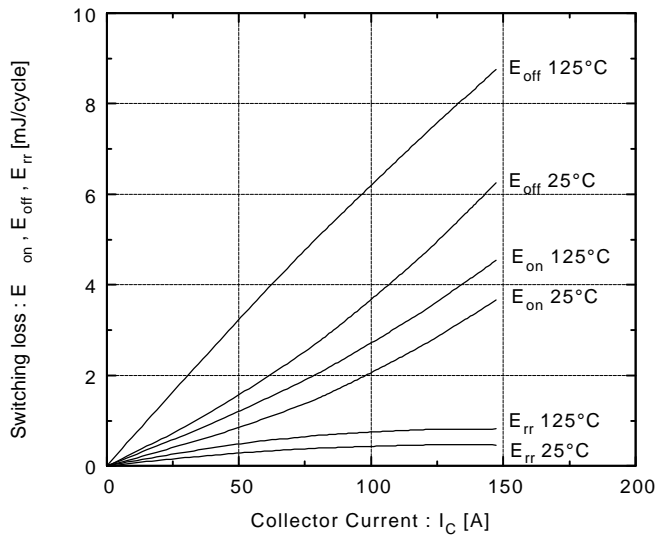


Reversed biased safe operating area

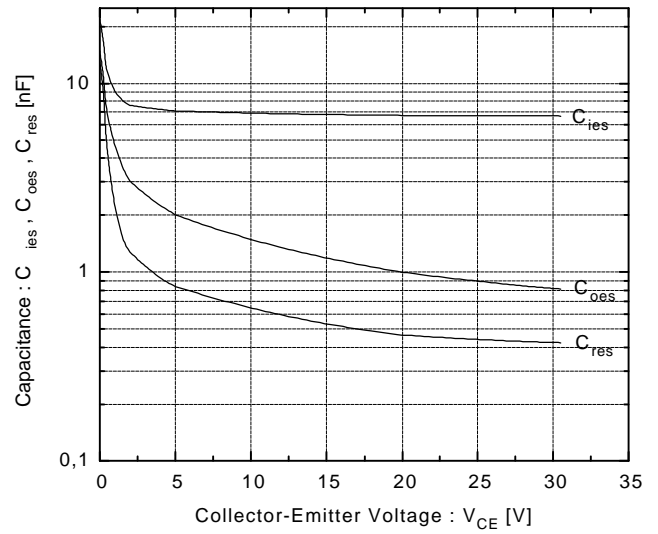
$+V_{GE}=15V$ ,  $-V_{GE}\leq 15V$ ,  $T_J\leq 125^\circ C$ ,  $R_G\geq 24\Omega$



Switching loss vs. Collector current

 $V_{CC}=300V$ ,  $R_G=24\Omega$ ,  $V_{GE}=\pm 15V$ 

Capacitance vs. Collector-Emitter voltage

 $T_J=25^\circ C$ **Fuji Electric GmbH**

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